## **Supporting Information**

# Multifunctional pseudohalide-based ionic liquid doping promotes efficient and stable perovskite solar cells

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## **Experiment section**

#### Materials

The Tin (IV) oxide (SnO<sub>2</sub>, 15% in H<sub>2</sub>O colloidal dispersion is purchased from Alfa Aesar. Lead iodide (PbI<sub>2</sub>, 99.99%), Lead chloride (PbCl<sub>2</sub>, 99.99%), and Cesium iodide (CsI, 99.99%) are purchased from Xi'an Polymer Light Technology Corp. Lead bromide (PbBr<sub>2</sub>, 99.99%), Cesium bromide (CsBr, 99.99%), Methylammonium iodide (MAI, 99.9%), Formamidinium iodide (FAI, 99.9%), and spiro-OMeTAD (99.86%) are purchased from Advanced Election Technology Co. Ltd. The N,N-Dimethylformamide (DMF, 99.8%), isopropanol (IPA, 99.5%) and chlorobenzene (CB, 99.5%) are purchased from Sigma-Aldrich. All materials are purchased without further purification.

## **Device fabrication**

The indium tin oxide (ITO) substrates were cleaned sequentially with detergent, deionized water, and ethanol in an ultrasonic wave for 20 min, respectively. The substrate was treated with UV-ozone for 20 min before depositing SnO<sub>2</sub>. The diluted SnO<sub>2</sub> solution (5%) was spin-coated on the ITO substrates at 4000 rpm for 30 s, then the substrates were annealed at 150 °C for 30 min on a hot plate. After cooling down to room temperature, the substrates were treated with UV-ozone for 5 min. After that, the substrates were transferred into a nitrogen-filled glove box. The perovskite films were fabricated by a two-step process. 1.36 M PbI<sub>2</sub>, 0.24 M PbCl<sub>2</sub>, and 0.08 M CsI were dissolved in the DMF and stirred for 3 h at 70 °C. 70 mg MAI and 30 mg FAI were dissolved in 1 mL IPA with 10 µL DMF added. For the TEAPF<sub>6</sub> doped precursor, the  $\ensuremath{\mathsf{TEAPF}}_6$  with different concentrations was added to the  $\ensuremath{\mathsf{PbX}}_2$  solution.  $PbX_2$  precursor solution was spin-coated onto  $SnO_2$  substrates at 3000 rpm for 45 s. Then, 200  $\mu$ L MAI:FAI solution was spin-coated onto the PbX<sub>2</sub> at 3000 rpm for 45 s, immediately. Then the samples were thermally annealed on a hot plate at 100 °C for 10 min. After cooling to room temperature, the spiro-OMeTAD was spin-coated on the top of the perovskite layer at 4000 rpm for 45 s. The spiro-OMeTAD solution was prepared by dissolving 72.5 mg spiro-OMeTAD, 17.5 µL Li-TFSI solution (520 mg/mL in acetonitrile), 28.8 µL FK209 solution (300 mg/mL in acetonitrile), and 28.8 µL 4-tertbutylpyridine (tBP) in 1 mL chlorobenzene. Finally, 100 nm Ag was deposited on the top of spiro-OMeTAD by thermal evaporation as the electrodes. The area of the device is 7.5 mm<sup>2</sup> defined by shadow mask.

## Characterization

The XRD spectra were performed by Bruker D8 Advance XRD. The UV-vis absorption spectra were measured by Perkin-Elmer Lambda 950 spectrophotometer. The PL and TR-PL spectra were measured by the Pico Quant Fluotime 300 with a 510 nm picosecond pulsed laser. The SEM images were measured by SEM JSM-7800F. XPS measurements were measured by the Escalab 250Xi with a source of monochromatic Al-Ka (1486.6 eV). The current-voltage curves of devices were tested by Keithley 2400 source meter under AM 1.5G irradiation with a luminous power of 100 mW cm<sup>-2</sup>. The EQE spectra were measured by the SCS10-X150 systems (Zolix instrument. Co. Ltd). TPC spectra were measured by a digital oscilloscope (Tektronix, D4105) with a sampling resistor of 50  $\Omega$  under a 532 nm (1000 Hz, 3.2 ns) pulse laser. TPV spectra were measured by the same system with a sampling resistor of 1 M $\Omega$  under a 405 nm (50 Hz, 20 ms) pulse laser. The *C-V* and EIS spectra were measured by an electrochemical workstation (Jiangsu Donghua Analysis Instruments Co., Ltd, DH7001).

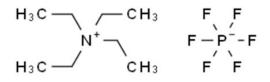


Figure S1. The chemical structure of TEAPF<sub>6</sub> ILs.

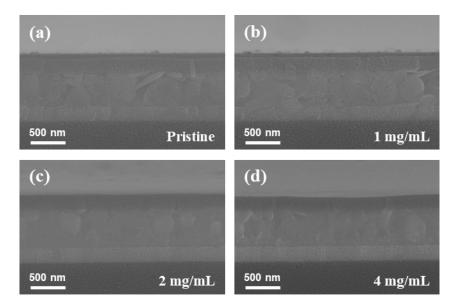


Figure S2. Cross-section SEM images of perovskite films with different concentrations of  $TEAPF_6$ .

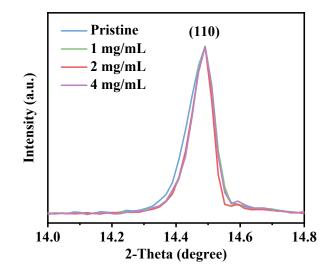


Figure S3. The FWHM of (110) peak of perovskite films in Figure 1e.

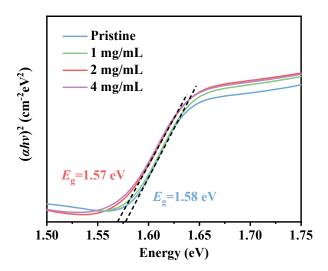


Figure S4. Tauc plots of perovskite films with different concentrations of TEAPF<sub>6</sub>.

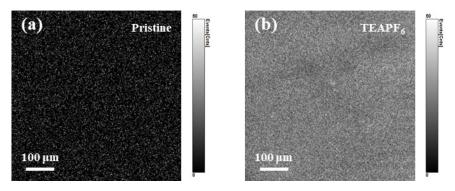


Figure S5. PL mappings of (a) pristine and (b) TEAPF<sub>6</sub> doped perovskite films.

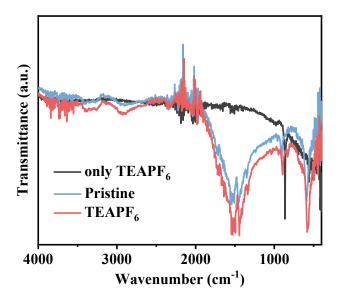


Figure S6. FTIR spectra of perovskite films without and with TEAPF<sub>6</sub> doping.

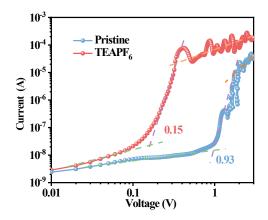


Figure S7. The dark I-V curves of the electron-only devices based on perovskite without and with TEAPF<sub>6</sub>.

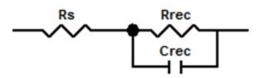


Figure S8. The equivalent circuit for fitting EIS curves.

**Table S1.** Fitting parameters of TR-PL curves of perovskite films without and with TEAPF<sub>6</sub>.

Conditions	$A_1$	$\tau_1$ (ns)	$A_2$	$\tau_2$ (ns)	$ au_{\mathrm{ave}}\left(\mathrm{ns} ight)$
Pristine	0.84	9.46	0.16	80.35	52.95
1 mg/mL TEAPF <sub>6</sub>	0.72	22.07	0.28	143.65	109.68
2 mg/mL TEAPF <sub>6</sub>	0.53	35.62	0.47	204.70	176.87
4 mg/mL TEAPF <sub>6</sub>	0.54	26.07	0.46	166.89	145.41

Table S2. The *J-V* parameters of PSCs with different concentrations of TEAPF<sub>6</sub>.

Conditions		$J_{ m SC}$	V <sub>OC</sub>	FF	PCE
Conditions		$(mA/cm^2)$	(V)	ГГ	(%)
Pristine	Average	22.96	1.09	0.77	19.27
	Best	23.89	1.10	0.77	20.23

1 mg/mL	Average	23.15	1.11	0.76	19.53
TEAPF <sub>6</sub>	Best	24.15	1.11	0.79	21.28
2 mg/mL	Average	23.39	1.14	0.78	20.80
TEAPF <sub>6</sub>	Best	24.26	1.15	0.79	22.13
3 mg/mL	Average	23.21	1.12	0.77	20.02
TEAPF <sub>6</sub>	Best	23.89	1.14	0.79	21.52
4 mg/mL	Average	23.03	1.11	0.76	19.43
TEAPF <sub>6</sub>	Best	23.19	1.14	0.76	20.09

**Table S3.** The J-V parameters of PSCs without and with TEAPF<sub>6</sub> in different scan directions.

Conditions	Scan	$J_{ m SC}$	V <sub>OC</sub>	FF	PCE	HI
	directions	(mA/cm <sup>2</sup> )	(V)	(%)	(%)	(%)
D : .:	RS	23.33	1.11	0.77	19.94	21.65
Pristine	FS	23.07	1.11	0.61	15.62	21.65
TEAPF <sub>6</sub>	RS	23.84	1.14	0.79	21.47	14.00
	FS	23.41	1.14	0.69	18.41	14.23

**Table S4.** Fitting parameters of the EIS curves of PSCs.

61			
Conditions	$R_{ m S}\left(\Omega ight)$	$R_{ m rec}\left(\Omega ight)$	$C_{rec}\left(\mathrm{F} ight)$
Pristine	60.93	$2.08 \times 10^{6}$	6.45×10 <sup>-9</sup>
With TEAPF <sub>6</sub>	41.48	3.09×10 <sup>6</sup>	5.82×10-9